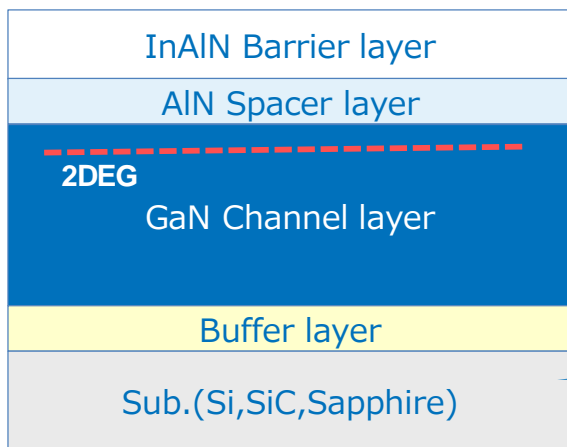


InAlN / GaN HEMT

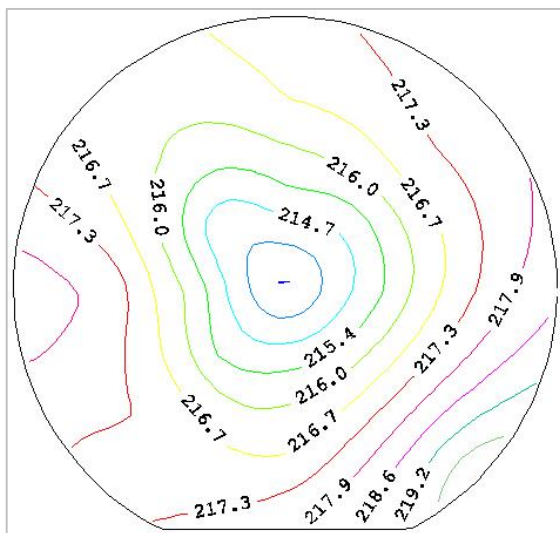
For next generation high frequency and high output power devices

■ Typical Structure



Si: up to **8** inch
 SiC: up to **4** inch
 Sapphire: up to **3** inch

■ Sheet resistivity distribution on 6 inch InAlN/GaN HEMT and hall effect



Ave.: 216 ohm/sq. (Var.: 3.6%)

Hall

Rs [ohm/sq.]	219
μ [cm ² /Vs]	1300
Ns[cm ⁻²]	2.20e13

*Some of the specifications may change without prior notice.

For Further Inquiry

<http://www.ntt-at.com/>